

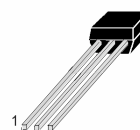
**HC114T****APPLICATIONS**

Switching Circuit , Interface Circuit.

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg}	Storage Temperature.....	-55~150
T_j	Junction Temperature.....	150
P_C	Collector Dissipation.....	300mW
V_{CBO}	Collector-Base Voltage.....	50V
V_{CEO}	Collector-Emitter Voltage.....	50V
V_{EBO}	Emitter-Base Voltage.....	5V
I_C	Collector Current.....	100mA

TO-92S



- 1 Emitter , E
- 2 Collector,C
- 3 Base , B

ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	50			V	$I_C=50 \mu A, I_E=0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	50			V	$I_C=1mA, I_B=0$
BV_{EBO}	Emitter-Base Breakdown Voltage	5			V	$I_E=50 \mu A, I_C=0$
I_{CBO}	Collector Cut-off Current			0.1	μA	$V_{CB}=50V, I_E=0$
I_{EBO}	Emitter Cut-off Current			0.1	μA	$V_{EB}=4V, I_C=0$
H_{FE}	DC Current Gain	100		600		$V_{CE}=5V, I_C=1mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			0.3	V	$I_C=10mA, I_B=1mA$
$V_I (off)$	Input Off Voltage	0.4	0.55	0.8	V	$V_{CE}=5V, I_C=0.1mA$
$V_I (on)$	Input On Voltage	0.7	1.2	3.0	V	$V_{CE}=0.2V, I_C=10mA$
R_I	Input Resistor	7.0	10	13	K	
f_T	Current Gain-Bandwidth Product		250		MHz	$V_{CE}=10V, I_C=5mA$
C_{ob}	Output Capacitance		3.7		pF	$V_{CB}=10V, f=1MHz$